Stability of negative and positive trions in quantum wires

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B inding energies of negative (X) and positive trions (X $^+$) in quantum wires are studied for strong quantum con nement of carriers which results in a numerical exactly solvable model. The relative electron and hole localization has a strong e ect on the stability of trions. For equal hole and electron con nement, X $^+$ is more stable but a small in balance of the particle localization towards a stronger hole localization e.g. due to its larger e ective mass, leads to the interchange of X and X $^+$ recombination lines in the photolum inescent spectrum as was recently observed experimentally. In case of larger X stability, a magnetic eld oriented parallel to the wire axis leads to a stronger increase of the X $^+$ binding energy resulting in a crossing of the X $^+$ and X lines.

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I. IN TRODUCTION

Trions are charged exciton complexes form ed when an electron or a hole is bound¹ to a neutral exciton (X). The binding energies of the complexes are very small in bulk, but they are substantially enhanced in structures of reduced dimensionality, i.e., in quantum wells^{2,3,4,5,6,7,8} and quantum wires.^{9,10,11}

Due to the larger e ective m ass of the hole, in $bulk^{12}$ as well as in strictly two-dimensional con nement³ the binding energy of positive trions (X^+) is larger than the negative trion (X) binding energy. However, in quantum wells the observed 5 X and X $^{+}$ binding energies are nearly equal, which is explained^{4,5} by a stronger hole localization within the quantum well enhancing the hole-hole interaction. The magnetic eld perpendicular to the plane of con nem ent enhances more strongly the stability leading to a crossing of X and X + binding Х energies.^{13,14} For trions localized on a defect of the quantum wellpotentialX can becomemore stable than X ⁺ even without the presence of an external magnetic eld.¹⁵ The combined quantum well and defect con nem ent creates a three-dim ensional potential similar to a quantum dot. In quantum dots the localization-related hole-hole interaction enhancem ent leads to the interchange of the order of the X and X⁺ recombination lines in the photolum inescence (PL) spectrum already for quantum dot diam eters as large as 24 donor Bohr radii.¹⁶ For sm aller dots the X $^+$ line becomes even more energetic^{16,17} than the X line. In coupled dots $1^{7,18}$ this e ect leads to the ground-state dissociation of X^{+} ,^{17,18} for which the holes in the ground state occupy di erent dots.

The present work is motivated by a recent experim ental study¹¹ of positive and negative exciton trions in V-groove G aA s/A G aAs quantum wires. The negative trion was found to be distinctly more stable than X⁺ (binding energies of X and X⁺ were determined as 4.2 and 2.9 meV, respectively). Here, we indicate that the observed¹¹ order of X and X⁺ energy lines may be a

consequence of m odi cations of the interactions due to a stronger hole con nem ent. In a previous theoretical study⁹ of trions in quantum wires X⁺ was found to be m ore stable than X , which was obtained in the case of equal hole and electron con nem ent. A crossing of X and X⁺ PL lines as functions of the wire width has previously been obtained in a quantum M onte-Carlo study¹⁰ of a quantum wire with a square well con nem ent potential. In this paper we focus on the e ect due to di erent electron and hole localization leading to modi cations of the e ective inter-particle interactions. W e study the correlations between electrons and holes and consider the e ectofam agnetic eld oriented parallel to the quantum w ire. The study of the stability of the trions is perform ed as function of the electron and hole localization instead of dimensions of the wire. It has been demonstrated¹⁹ that in realistic quantum wires with strong con nem ent the binding energy of neutral excitons is governed by a size dependent param eter independent of the shape and composition of the wire.

The stronger hole localization results from its weak penetration into the barrier material due to its larger e ective mass than the electron band mass. For the spillover of the electron wave function out of the quantum wire, recently observed in self-assem bled InA s/InP quantum wires,²⁰ the ratio of the electron to hole localization can in principle be arbitrarily large.²⁰ How ever, in the following we show that even a small enhancement of the hole localization changes the order of the X and X ⁺ PL recombination lines.

For the purpose of the present study we apply the single band model for the hole and consider a harmonic oscillator con nement potential in the directions perpendicular to the wire, referred to as "lateral" in the following. The present model does not account for the interface between the wire and barrier materials, so the e ective mass discontinuity and dielectric constant m ismatch are neglected. These e ects usually strengthen the electron-hole interaction and weaken the penetration of the wave functions into the barrier. They are how ever of a secondary im portance for G aA s/A G aA s,²¹ InA s/InP,²² and CdTe/ZnTe²³ quantum wires. Note that, the present modelling is inapplicable to the free-standing quantum wires, where the image charge e ect is extrem ely strong.²⁴

We assume that the lateral con nement is strong, so that only the lowest subband for the electron and hole is occupied. This assumption allows for a reduction of the Schrödinger equation to an elective two-dimensional form. U sually the solution of the trion eigenequations is very challenging and requires extensive variational calculations^{2,3,4,6,7,12,16,17} or application of the quantum M onte C arbom ethods.^{10,15} The present problem is unique in the sense that it allows for an exact inclusion of the interparticle correlations.

The paper is organized as follows: the next Section contains the theory, the results are given in Section III, the conclusion and sum m ary are presented in Section IV.

II. THEORY

We adopt the donor units, i.e., donor Bohr radius $a_d = 4_{-0} h^2 = m_e e^2$ for the unit of length and twice the donor Rydberg $2R_d = h^2 = m_e a_d^2$ as the unit of the energy, where m_e is the band electron e ective m ass and is the dielectric constant. In these units, the H am iltonian for a single electron in a quantum wire with harm onic oscillator lateral con nem ent has the form

$$H_{e} = \frac{1}{2} \frac{\theta^{2}}{\theta z_{e}^{2}} + H_{e}^{1};$$
 (1)

with the lateral H am iltonian

$$H_{e}^{1} = \frac{1}{2} \frac{\theta^{2}}{\theta x_{e}^{2}} + \frac{\theta^{2}}{\theta y_{e}^{2}} + \frac{1}{2t_{e}^{4}} (x_{e}^{2} + y_{e}^{2}); \quad (2)$$

where l_e is the length of the harm onic oscillator con nement for the electron. The ground-state wave function of the Ham iltonian (2) is $_e = \exp\left[(x^2 + y^2) = 2l_e^2 \right] = l_e^{D}$ with the energy eigenvalue $E_e = 1 = l_e^2$. In the adopted single-band approximation the hole ground-state wave function ($_h$) of the lateral con nement has the form of $_e$ but with l_h -the harm onic oscillator length for the hole instead of l_e , and the energy is $E_h = 1 = l_h^2$, where

= $m_h = m_e$ is the hole to electron e ective mass ratio, or, in other words, the hole mass in the donor units. The negative trion H am iltonian can be written as

$$H = H_{e1} + H_{e2} + H_h - \frac{1}{r_{e1h}} - \frac{1}{r_{e2h}} + \frac{1}{r_{12}}; \quad (3)$$

where r_{elh} (r_{e2h}) is the distance between the rst (second) electron and the hole and r_{12} is the electron-electron distance. We assume that the lateral con nement is sufciently large that the trion wave function can be electron-tively separated into a product

$$(\mathbf{r}_{e1};\mathbf{r}_{e2};\mathbf{r}_{h}) = (\mathbf{x}_{e1};\mathbf{y}_{e1}) (\mathbf{x}_{e2};\mathbf{y}_{e2}) (\mathbf{x}_{h};\mathbf{y}_{h}) (\mathbf{z}_{e1};\mathbf{z}_{e2};\mathbf{z}_{h});$$
(4)

where is the negative trion wave function of the motion along the wire. The H am iltonian (3) integrated over the lateral degrees of freedom with the wave function (4) produces the elective trion H am iltonian:

$$H^{ef} = \frac{1}{2} \frac{\theta^{2}}{\theta z_{e1}^{2}} + \frac{\theta^{2}}{\theta z_{e2}^{2}} - \frac{1}{2} \frac{\theta^{2}}{\theta z_{h}^{2}} + V^{ef}(l_{e}; z_{e1} - z_{e2}) - V^{ef}(l_{eh}; z_{e1} - z_{h})$$

$$V^{ef}(l_{eh}; z_{e2} - z_{h});$$
(5)

with $l_{eh} = \frac{p}{(l_e^2 + l_h^2)=2}$ and the elective interaction potential^{9,25}

$$V^{ef}(l;z) = (=2)^{1=2} \operatorname{erfc}(z; = 2l) \exp(z^2 = 2l^2) = l;$$
 (6)

which is nite at the origin (V ^{ef}(l;0) = 1=1) and approaches the 1=z asymptotic at large z. Hamiltonian (5) is written with respect to the sum of the ground-state energies of noninteracting two electrons and one hole. Therefore, the absolute value of the (negative) energy of a bound state is interpreted as the energy needed to separate all the particles away from one another. Introducing the center-offm ass coordinate $Z = (z_{e1} + z_{e2} + z_h) = (2 +)$ one obtains $H^{ef} = \frac{1}{2M} \frac{e^2}{eZ^2} + H^{rel}$, where M = 2 + is the negative trion m ass and H ^{rel} is the relative m otion H amiltonian

$$H^{\text{rel}} = \frac{1}{2} \frac{\theta^{2}}{\theta z_{h1}^{2}} + \frac{\theta^{2}}{\theta z_{h2}^{2}} \frac{1}{\theta z_{h1}^{2}} \frac{\theta^{2}}{\theta z_{h1} \theta z_{h2}}$$

$$+ V^{\text{ef}}(l_{e}; z_{h1} z_{h2}) V^{\text{ef}}(l_{eh}; z_{h1}) V^{\text{ef}}(l_{eh}; z_{h2});$$

$$(7)$$

with the reduced mass of an electron-hole pair = =(1 +), and the coordinates of the relative electron-hole positions $z_{h1} = z_h \quad z_{e1}$ and $z_{h2} = z_h \quad z_{e2}$. In these coordinates the inter-electron distance along the length of the wire is $z_{12} = j z_{h1} \quad z_{h2} j$. The wave function is separable into a product of the center of mass and relative wave function $(z_{e1}; z_{e2}; z_h) = {}_{CM} (Z) (z_{h1}; z_{h2}).$

The corresponding relative Ham iltonian for the positive trion has the following form :

$$\begin{aligned} H_{+}^{rel} &= \frac{1}{2} \frac{\theta^{2}}{\theta z_{h1}^{2}} + \frac{\theta^{2}}{\theta z_{h2}^{2}} \frac{\theta^{2}}{\theta z_{h1} \theta z_{h2}} \\ &+ V^{ef}(I_{h}; z_{h1} z_{h2}) V^{ef}(I_{eh}; z_{h1}) \\ V^{ef}(I_{eh}; z_{h2}); \end{aligned}$$
(8)

with z_{h1} , z_{h2} standing here for the relative position coordinates of the rst and second hole with respect to the electron position. The reference energy for the H am iltonian (8) is the energy of the dissociated com plex, i.e., $2E_{h} + E_{e}$.

In the following we consider also the exciton for which the e ective H am iltonian written with respect to the energy of a dissociated electron and hole pair reads

$$H^{X} = \frac{1}{2} \frac{\theta^{2}}{\theta z_{eh}^{2}} \quad V^{ef}(\underline{l}_{eh}; z_{eh}):$$
(9)

The lowest eigenvalue of this H am iltonian is equal to m inus the exciton binding energy (E_B^X). On the other hand the di erence between E_B^X and the eigenvalues of trion H am iltonians (7,8) is equal to the trion binding energies (E_B^X , $E_B^{X^+}$) with respect to dissociation into an exciton and a free electron (for X) or a hole (for X⁺). Trion binding energies are equal to the red-shift of the trion recombination lines with respect to the exciton line in the PL spectrum.



FIG.1: (a) [color online] C ontour plot of the interaction potential V = V $^{\rm ef}$ (L; z_{h1} z_{h2}) V $^{\rm ef}$ (L; z_{h1}) V $^{\rm ef}$ (L; z_{h2}) as function of the interparticle distances with lateral con nem ent length L = l_e = l_h = 1. D istances and energies are given in donor units. The dashed-dotted line corresponds to V = 0. (b) The interaction potential plotted for L = 1 along the lines z_{h2} = z_{h1} , z_{h2} = z_{h1} 1.5, and z_{h2} = z_{h1} 3 m arked in (a) with (thick) solid, dotted and dashed lines respectively, as function of the interelectron (X) or interhole (X $^+$) distance z_{12} = z_{h1} z_{h2} . Thin solid line shows the $3=jz_{12}j$ asymptotic.

W e solve the relative H am iltonian eigenequations using the imaginary time technique²⁶ on a two-dimensional grid with a nite-di erence approach. We use 201 points in both z_{h1} and z_{h2} directions. The size of the computational box in both directions is chosen "self-consistently" to be 12 times larger than the average distance between the particles of the same charge de ned as <

 $(z_{h1} \quad z_{h2}) > {}^{1=2}$.

In the present calculations we assumed harm onic oscillator lateral con nem ent which allows us to simplify the problem considerably because of the availability of analytical form ula^{9,25} for the e ective one-dimensional interaction. The con nem ent lengths le and la param etrize the strength of the particle localization. Since the singleparticle energies cancel in the calculation of the trion binding energies, the applicability of the present results is wider. In fact the present results can be used for any form of the lateral con nem ent (which does not even have to be cylindrically sym m etric) as long as it produces the same e ective interaction potential. For instance the electron-electron interaction potential for $l_e = 2.95$ and 6 nm is very well (i.e. with a precision better than 2%) reproduced for a G aA s quantum wire ($m_{e} = 0.067$) with a circular square well con nem ent of depth 320 m eV and diam eters 9.6 nm and 22.8 nm respectively. For elliptical harm onic oscillator con nem ent with di erent oscillator lengths in x and y directions $(l_x \text{ and } l_y, \text{ respectively})$ we cannot give a closed analytical form ula for the e ective interaction potential. Nevertheless, we have found via a num erical integration that the interaction potential between two electrons in an elliptical wire can be surprisingly well reproduced by form ula (6) for a circular wire with an e ective $l = (l_x + l_y) = 2$. The num erically calculated deviation between the two potentials is not larger than 2% for any interelectron distance. The essential assum ption of the present m odel therefore does not rely on the form of the lateral con nem ent but on its strength, which has to be large enough to prevent the Coulomb interactions from deforming the lateral wave functions. The applied assumption of the frozen lateral degrees of freedom for the electron and the hole is applicable for the exciton binding energy when $l_e < a_d$ and $l_h < a_d$. This condition guarantees that the length of the lateral connem ent of the carriers is smaller than the bulk exciton radius, and that the sum of the lateral con nem ent energies for the electron and the hole are at least two times larger than the exciton binding energy in bulk. For trions the applied approximation is better justi ed and the conditions are less stringent because the trions have a larger size and have sm aller binding energies than the exciton.

III. RESULTS

W e start the presentation of our results by discussing the properties of trions in quantum wires with equal lateral con nem ent for the electron and the hole (subsection IIIA), and then in subsection IIIB we show the e ect of di erent con nem ents for the stability of X $^+$ and X $\,$ trions. Subsection IIIC describes the e ect of the magnetic eld oriented parallel to the axis of the wire.



FIG.2: W ave functions for negative (a,d,g,j) and positive (b,c,e,f,h,i,k,l) trions for $l_e = l_h = L = 0.2$ in z_{h1} and z_{h2} coordinates (horizontal and vertical axis, respectively) for di erent values of the mass ratio . P lots (c,f,i,l) show the wave functions of the excited X⁺ state antisym metric with respect to the interchange of the holes. The dashed line in (f,i,l) shows the node of the wave functions. P lot (c) corresponds to an unbound state, for other plots the computational box is larger than the fragment displayed and the states are bound.

 ${\tt A}$. Identical electron and hole lateral con ${\tt nem ent}$

For equal electron and hole lateral con nem ent ($l_e = l_h = L$) the electron-electron, the hole-hole, and the electron-hole interactions have the same form . The total interaction potential, identical for both types of trions, is plotted in Fig. 1 (a) as function of z_{h1} and z_{h2} for L = 1. The regions of positive (negative) potentials are

plotted with red (blue) colors. Zero of the interaction potential is marked with a dash-dotted line. The interaction potential is minimal along the lines $z_{\rm h1}=0$ and $z_{\rm h2}=0$ at which one of the two electrons and the hole are in the same position (for X $\)$ or the position of one of the holes coincides with the electron position (for X $^+$). The potential is maximal along the diagonal $z_{\rm h1}=z_{\rm h2}$ at which the two particles of the same charge are localized in the same point along the wire length. Fig. 1 (b) shows



FIG. 3: Electron-hole (solid lines), electron-electron, hole-hole (dashed lines) pair correlation functions plots for X and X $^+$ (lines marked by black squares) at ~=~6:72 and l_e = l_h = 0.2.



FIG. 4: B inding energies of the negative (dashed lines) and positive trion (solid lines) states for L = 0.2 as function of the m ass ratio . H igher solid curve corresponds to the X⁺ state antisym m etric with respect to the interchange of electrons and holes, i.e. it is the rst excited state. Thin vertical lines show the values of = 1;1:98;6:72 and 15.2. D otted curve, referred to the right axis, show s the exciton ground-state eigenvalue. Energies and lengths are in donor units.

the cross-sections of the interaction potential along the three straight lines in Fig. 1 (a) as function of the interelectron (X) or interhole (X⁺) distance z_{12} . On the antidiagonal the interaction has the form of a triangular potential well [cf. solid line in Fig. 1 (b)]. Moving along the antidiagonal is equivalent to interchange the position of the two particles of the same charge with xed position of the third particle of the opposite charge. A long the paths plotted with dotted and dashed lines in Fig. 1 (a), which are shifted below the antidiagonal, the potential has the form of a double potential well [see Fig. 1 (b)] with a barrier near the diagonal resulting from the



FIG.5: [color online] B inding energies of the trions as functions of the length of the lateral con nement. Lines for

= 1;1:98;6:72 and 15.2 plotted with black, blue, red, and green colors, respectively. For = 1 binding energies of X and X⁺ are equal. The dashed lines are the energies of the excited X⁺ states antisymmetric with respect to the interchange of the holes (X does not possesses a bound excited state for > 1). Lines for X at = 1:98 and 6.72 have been om itted for clarity - they are situated between the = 1 line and = 15.2 line for X (see Fig. 4). Inset: energy eigenvalues for neutral exciton and charged trions for = 15.2. Energies and lengths are given in donor units.

repulsion of the equally charged particles. For large z_{12} the potential approaches $3=z_{12}$ asymptotically which is shown by the this solid line in Fig. 1 (b).

Contourplots of the wave function of the negative and positive trions calculated for di erent e ective m ass ratios are plotted in Fig. 2 for L = 0.2. For L = 1, the negative and positive trion relative H am iltonians (7) and (8) di er only by the factor standing in front of the mixed derivative (1 = for X and 1 for X^+). The ground-state wave function for = 1 is the same for both trions [cf. Figs. 2 (a,b)]. The rst excited state of X⁺, which is antisymmetric with respect to the interchange of the holes is unbound. Its wave function calculated for the size of the computational box 100 100 (in donor Bohr radius units) is plotted in Fig. 2 (c). For the unbound state no com putational box is large enough (i.e. the wave function vanishes only at the ends of the computational box). The wave function is nonzero only near both axis. One of the holes stays at the position of the electron and the other strives to be as far as possible from the other two particles.

Results for = 1:98 plotted in Figs. 2(d-f) correspond to CdTe material parameters ($m_h = 0.19m_0$, $m_e = 0.096m_0$) with the donor units $a_d = 5:4$ nm and $2R_d = 27:6$ meV. The probability density maximum for = 1 is split into two extrem a at the antidiagonal of the plots [cf. Figs. 2(a-b)]. For > 1 these two extrem a merge into a single one for X [see Fig. 2(d)] and for X⁺ they become more distinctly separated [see Fig. 2(e)] and the excited state for X⁺ becomes bound [cf. Fig. 2(f)].



FIG.6: [color online] Contour plot of the interaction potential for (a) negative trion $V = V^{ef}(l_e; z_{h1} z_{h2}) V^{ef}(l_{eh}; z_{h1}) V^{ef}(l_{eh}; z_{h2})$ and (b) positive trion $V = V^{ef}(l_h; z_{h1} z_{h2}) V^{ef}(l_{eh}; z_{h1}) V^{ef}(l_{eh}; z_{h2})$ as function of the interparticle distances for the lateral con new ent lengths $l_e = 1$ and $l_h = 0.5$. Distances and energies are given in donor units.



FIG.7: [color online] Shifts of the trion recombination PL lines with respect to the PL exciton line as function of the hole con nem ent length (l_h) for G aAs. D i erent values of the electron con nem ent length are plotted with di erent colors.

Figs. 2(q-i) and 2(i-1) for = 6:7 and = 152correspond to GaAs ($m_h = 0.45m_0$, $m_e = 0.067m_0$, $2R_d = 11.9 \text{ meV}$, $a_d = 9.8 \text{ nm}$) and InAs (m $_h = 0.41 \text{ m}_0$, $m_{e} = 0.027m_{0}, 2R_{d} = 3.2 \text{ meV}$ and $a_{d} = 29.7 \text{ nm}$) material parameters, respectively. Increasing has an opposite e ect on the X \quad and X $^+$ wave functions. For the negative (positive) trion the localm in im um along the diagonal $z_{h1} = z_{h2}$ is less (m ore) pronounced. The wave function evolution with is related to the tunnelling of the particles of the sam e charge via the potential barrier presented in Fig. 1 (b). The electrons in X with light effective m asses tunnel easily through the diagonal barrier due to the interelectron repulsion. On the other hand the diagonal barrier is e ectively much larger for the heavymass holes which prevents its penetratation at large which leads to the appearance of the characteristic maxin a elongated along the diagonal in Figs. 2(e,h,k).

The correlation between the particles in the com plexes is more clearly visible in the pair correlation functions plotted in Fig. 3. The electron-hole correlation function is calculated as $f_{eh}\left(z\right)=dz_{h1}dz_{h2}j~(z_{h1};z_{h2})\mathring{f}~(z_{z_{h1}})$ and the hole-hole (for $_{R}X^{+}$), and electron-electron (for X) as $f_{sam}~(z)=dz_{h1}dz_{h2}j~(z_{h1};z_{h2})\mathring{f}~[z~(z_{h1}-z_{h2})]$. The Coulom b hole in the hole-hole correlation in X^{+} ism uch larger than for electron-hole localization.

The binding energies of the exciton and the trions for L = 0.2 are plotted as functions of in Fig. 4. All the binding energies are increasing functions of . In bulk the rst excited state of the positive trion is antisym metric with respect to the hole interchange, 27 possess the P symmetry and is bound for > 42. The critical value of the m ass ratio is m uch sm aller for quasi 1D con nem ent.⁹ Here, for L = 0.2 the excited X⁺ state is bound for > 1.2 (see Fig. 3). For quasi1D con nem ent the low est excited state has the S sym m etry with respect to the axis of the wire but is of odd spatial parity, i.e., it is antisymm etric with respect to simultaneous change of sign of all the z coordinates (see Fig. 2). The groundstate of X⁺ becom es degenerate with respect to the sym m etry of the wave function, i.e., the hole interchange, for large for which tunnelling through the diagonal potential barrier (cf. Fig. 1) disappears. At large also the probability density of the excited X + level becom es identical to the ground-state probability density (cf. Fig. 2). does not possesses a bound excited state for > 1. Х

The inset to Fig. 5 shows the ground-state energy for

= 152 as function of the lateral con nem ent length. In the L = 0 lim it the average interparticle distances decrease to zero and the energies diverge to m inus in nity. This is a consequence of the C oulom b interaction singularity in one dimension.²⁸ The main part of Fig. 5 shows the shifts of the trion PL lines with respect to the exciton line (calculated as the di erence of the eigenvalues presented in the inset) for di erent values of . It turns out that the binding energies have a power law dependence on L, i.e. L q , for the X and X $^{+}$ ground state presented in this gure q changes from 0.83 (= 1) to 0.91 (X $^{+}$ for = 15.2).

B. E ect of di erent electron and hole lateral con nem ent

Let us now consider the interaction potential for stronger hole con nem ent. Figs. 6(a) and (b) show the interaction potentials for l_e = 1 as in Fig. 1 but for smaller l_h = 0.5. For both the negative [cf. Fig. 6(a)] and the positive trion [cf. Fig. 6(b)] the potentialm inim a at z_{h1} = 0 and z_{h2} = 0 become deeper with respect to the l_e = l_h case presented in Fig. 1. For X the electron-electron interaction (the diagonal potential barrier) is not a ected by the change of l_h [com pare Fig. 1 and Fig. 6(a)]. On the other hand the hole-hole repulsive interaction for X $^+$ is strongly increased.



FIG.8: [color online] D i erence of the positive and negative trion binding energies (in meV) as function of the electron and hole con nem ent lengths for G aAs material parameters. B lue (red) regions correspond to more stable negative (positive) trion. A bove the dashed-dotted line the negative trion is unbound. The green line corresponds to E_B (X) = 4.2 meV and the yellow line to E_B (X ⁺) = 2.9 meV.

The elect of the hole localization on the trion binding energies is plotted in Fig. 7 for G aAs material parameters and xed values of the electron lateral connement. Consistently with the results of section III.A for $l_e = l_h$ the positive trion is more stable than the negative trion. A decrease of l_h below the value of l_e results in the interchange of the X and X $^+$ energy lines.²⁹ This is due to the enhanced hole-hole interaction shown in Fig. 6 (b). The negative trion binding energy is a monotonous function of the hole connement length, the larger l_h the smaller is the electron-hole interaction stabilizing X .



FIG.9: Interparticle distances for the negative (solid lines) and positive trions (dashed lines) and for the exciton (dotted line) for G aAs m aterial parameters and $l_{e} = 2.95$ nm. (e-e), (e-h), and (h-h) stand for the electron-electron, the electron-hole and the hole-hole distance.

The situation is more complex for X $^+$, since with increasing $l_{\rm h}$ also the destabilizing hole-hole interaction decreases. As a consequence the positive trion binding energy possesses a maximum as function of $l_{\rm h}$.

The di erence of the positive and negative trion binding energies is plotted in Fig. 8. Both the trions are equally stable for $l_{\!h}$ = 0:92 $l_{\!e}$ 0:38 nm . For $l_{\!h}$ larger (smaller) than 0:921, 0:38 nm X⁺ is more (less) stable than X . The maximum of the X^+ binding energy presented in Fig. 7 follows a path that is nearly linear for $l_{e} > 2$ nm and is approximately parametrized by $l_n = 1.62 l_e$ 1.98 nm. For the points at the left of the dash-dotted line the electron-hole attractive interaction stabilizing the trion is so weak with respect to the electron-electron repulsive interaction destabilizing the com plex that the negative trion stops to be bound (see also the line for X at $l_e = 2.95$ nm in Fig. 7). The absence of the negative trion binding requires a substantially weaker hole localization than the localization of the electron which is rather in possible to obtain in the presently produced quantum wires and would require the valence band o set between the wire and the matrix to be much sm aller than the conduction band o set. M oreover, the present m odelling based on the assumption that the lateral wave functions are not a ected by the interaction is likely to fail since the hole wave function is very likely to becom e m ore localized due to the attraction by strongly con ned electrons.

The tofthe calculated X and X⁺ binding energies to the experimental data is obtained at the crossing of the green and yellow lines, i.e., for $l_e = 2.95$ nm and $l_h =$ 1.3 nm. The obtained t corresponds to realistic values which give a general idea on the particle localization in the wire (the measurements¹¹ were performed on a Vgroove G aA s/A IG aA s quantum wire with a thickness of the G aA s crescent of 3 nm at the center). O byiously, a m ore realistic m odel is required to extract details of the con nem ent from the experim ental data.

The dependence of the size of the trion, i.e., the interparticle distance as function of the hole con nement length, is shown in Fig. 9 for $l_e = 2.95$ nm. The electronhole distance for the trions and the exciton have been calculated as $\overline{\langle z_{h1}^2 \rangle}$, and $\overline{\langle z_{eh}^2 \rangle}$, respectively. The hole-hole distance for X + and the electron-electron distance for X are determined as $(z_{h1} z_{h2})^2 > .$ The size of the exciton increases as ln increases which is due to the reduced value of the electron-hole interaction. M uch stronger dependence on l_h is observed for X , which becom es unbound for $l_h > 7$ nm [cf. Fig. 7]. The dependence of the X⁺ size on the hole con nem ent is nonmonotonous. The positively charged complex has the smallest size near $l_h = 3 \text{ nm}$ when it is the most strongly bound [cf. Fig. 7]. For $l_n = l_e = 2.95$ nm the order of the interparticle distances in the two com plexes is the same as in two-dimensional quantum wells (compare Fig. 4 of Ref. $[1^3]$). In spite of the fact that the probability of nding both holes in X^+ in the same position is much smaller than for electrons in X (cf. Fig. 3) the longer tail of the electron-electron correlation function results in a larger electron-electron distance than hole-hole distanœ.



FIG.10: [color on line] M agnetic eld dependence of the trion binding energies in G aAs for di erent values of the electron and hole oscillator lengths.

C. Magnetic eld parallel to the wire

In the present approach it is straightforward to include a magnetic eld oriented parallel to the axis of the wire. It simply scales down the electron and hole oscillator lengths according to the form ula $l(B) = (1=1^4 (0) + 1=1^4)^{1-4}$, where $l_c = \frac{1}{2h=eB}$ is the magnetic eld

length ($l_c = 3628 = B \text{ nm } T$). Since l(B) for high m agnetic elds decreases to l_c , the m agnetic eld tends to equalize the electron and hole localization. The binding energy of the trions can be obtained following paths of $(l_h (B); l_e (B))$ on Fig. (8). The modi cation of the binding energies of the trions by the magnetic eld is presented in Fig. 10 for di erent oscillator lengths. In a magnetic eld of 40 T, 1(B = 0) = 4.9 nm is decreased to 1(B = 40T) = 4:4 nm and 1(B = 0) = 6:86 nm to 1(B = 40T) = 5:19 nm. For $l_e = l_h = 6:86 \text{ nm}$ (see the red curves in Fig. 10) the magnetic eld decreases the length of con nem ent exactly as in the case presented in Fig. 5. In the more realistic case of stronger hole con nement, i.e., for $l_e = 6:86 \text{ nm}$ and $l_h = 4:9 \text{ nm}$ (see the black lines in Fig. 10) the magnetic eld increases the binding energy of the positive trion more strongly. This is because the magnetic eld more strongly a ects the larger le value than the smaller hole localization length l, which increases the electron-hole interaction m ore strongly than the repulsive hole-hole potential. For X the e ect of the increased electron-hole interaction is nearly cancelled by the increase of the electron-electron potential value. N ear 35 T a crossing of the black lines is observed, which corresponds to passing from the "blue" to the "red" region on the phase diagram of Fig. 8. This crossing is qualitatively opposite to the one obtained for two-dimensional quantum wells,¹³ in which a sm all magnetic eld (around 1 T) increased the X stability over the X⁺ binding energy. In quantum wells the magnetic-eld related increase of the single-particle energy is smaller for electrons and holes bound in the trion complex than for the lowest Landau level in the nal state of the free electron and hole after the trion dissociation. The crossing of the binding energies observed in quantum wires¹³ is therefore at least partially due to the stronger dependence of the electron lowest Landau level { note an alm ost linear magnetic eld dependence of the trion binding energies in Fig. 2 of Ref. $[1^3]$. In the present calculations the free electron and the free hole are strongly localized in the plane perpendicular to the eld and the single-particle magnetic eld e ects cancel due to the assumption of the frozen-lateral degrees of freedom, so that the crossing is entirely due to the modi ed e ective inter-particle interactions.

In the case of stronger electron con nem ent ($l_e = 4.9$ nm, $l_h = 6.86$ nm { the blue lines in Fig. 10) the situation is just opposite, the X is less strongly bound and the magnetic eld acts more strongly on the negative trion decreasing the binding energy di erence according to the mechanism described above. However, for the electron con nem ent equalor stronger than the hole con nem ent, the magnetic eld does not lead to crossing of the trion energy lines and X $^+$ is more stable for any magnetic eld.

W e studied the properties of the negative and positive trions in quantum wires with strong lateral con nem ent using the approxim ation of the lowest subband occupancy which allows for a num erically exact solution of the multi-particle Schrodinger equation. W e investigated the relative stability of the positive and negative trions with respect to the dissociation into an exciton and a free carrier for di erent electron and hole con nem ent. W e found that the order of the negative and positive trion P L lines is interchanged when the lateral con nem ent of the hole is stronger than the one for the electron. In a G aA s quantum wire with $l_{p} = 5$ nm we predict that when l_{p} is 20% sm aller the positive and negative trion recombination lines interchange. The change in the order is due to modi cation of the e ective interactions in the trion com plexes. The present results provide an explanation

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for the recently experim entally observed larger stability of the negative trion in quantum wires.¹¹ W e predict that for larger X stability due to stronger hole con nem ent the magnetic eld oriented parallel to the axis will tend to interchange the order of the X⁺ and X energy lines.

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- 29 The crossing point occurs exactly at l_{e} = l_{h} only for $\$ = 1.

Stability of negative and positive trions in quantum wires

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B inding energies of negative (X) and positive trions (X $^+$) in quantum wires are studied for strong quantum con nement of carriers which results in a numerical exactly solvable model. The relative electron and hole localization has a strong e ect on the stability of trions. For equal hole and electron con nement, X $^+$ is more stable but a small in balance of the particle localization towards a stronger hole localization e.g. due to its larger e ective mass, leads to the interchange of X and X $^+$ recombination lines in the photolum inescent spectrum as was recently observed experimentally. In case of larger X stability, a magnetic eld oriented parallel to the wire axis leads to a stronger increase of the X $^+$ binding energy resulting in a crossing of the X $^+$ and X lines.

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I. IN TRODUCTION

Trions are charged exciton complexes form ed when an electron or a hole is bound¹ to a neutral exciton (X). The binding energies of the complexes are very small in bulk, but they are substantially enhanced in structures of reduced dimensionality, i.e., in quantum wells^{2,3,4,5,6,7,8} and quantum wires.^{9,10,11}

Due to the larger e ective m ass of the hole, in $bulk^{12}$ as well as in strictly two-dimensional con nement³ the binding energy of positive trions (X^+) is larger than the negative trion (X) binding energy. However, in quantum wells the observed 5 X and X $^{+}$ binding energies are nearly equal, which is explained^{4,5} by a stronger hole localization within the quantum well enhancing the hole-hole interaction. The magnetic eld perpendicular to the plane of con nem ent enhances more strongly the stability leading to a crossing of X and X + binding Х energies.^{13,14} For trions localized on a defect of the quantum wellpotentialX can becomemore stable than X ⁺ even without the presence of an external magnetic eld.¹⁵ The combined quantum well and defect con nem ent creates a three-dim ensional potential similar to a quantum dot. In quantum dots the localization-related hole-hole interaction enhancem ent leads to the interchange of the order of the X and X⁺ recombination lines in the photolum inescence (PL) spectrum already for quantum dot diam eters as large as 24 donor Bohr radii.¹⁶ For sm aller dots the X $^+$ line becomes even more energetic^{16,17} than the X line. In coupled dots $1^{7,18}$ this e ect leads to the ground-state dissociation of X^{+} ,^{17,18} for which the holes in the ground state occupy di erent dots.

The present work is motivated by a recent experim ental study¹¹ of positive and negative exciton trions in V-groove G aA s/A G aAs quantum wires. The negative trion was found to be distinctly more stable than X⁺ (binding energies of X and X⁺ were determined as 4.2 and 2.9 meV, respectively). Here, we indicate that the observed¹¹ order of X and X⁺ energy lines may be a

consequence of m odi cations of the interactions due to a stronger hole con nem ent. In a previous theoretical study⁹ of trions in quantum wires X⁺ was found to be m ore stable than X , which was obtained in the case of equal hole and electron con nem ent. A crossing of X and X⁺ PL lines as functions of the wire width has previously been obtained in a quantum M onte-Carlo study¹⁰ of a quantum wire with a square well con nem ent potential. In this paper we focus on the e ect due to di erent electron and hole localization leading to modi cations of the e ective inter-particle interactions. W e study the correlations between electrons and holes and consider the e ectofam agnetic eld oriented parallel to the quantum w ire. The study of the stability of the trions is perform ed as function of the electron and hole localization instead of dimensions of the wire. It has been demonstrated¹⁹ that in realistic quantum wires with strong con nem ent the binding energy of neutral excitons is governed by a size dependent param eter independent of the shape and composition of the wire.

The stronger hole localization results from its weak penetration into the barrier material due to its larger e ective mass than the electron band mass. For the spillover of the electron wave function out of the quantum wire, recently observed in self-assem bled InA s/InP quantum wires,²⁰ the ratio of the electron to hole localization can in principle be arbitrarily large.²⁰ How ever, in the following we show that even a small enhancement of the hole localization changes the order of the X and X ⁺ PL recombination lines.

For the purpose of the present study we apply the single band model for the hole and consider a harmonic oscillator con nement potential in the directions perpendicular to the wire, referred to as "lateral" in the following. The present model does not account for the interface between the wire and barrier materials, so the e ective mass discontinuity and dielectric constant m ismatch are neglected. These e ects usually strengthen the electron-hole interaction and weaken the penetration of the wave functions into the barrier. They are how ever of a secondary im portance for G aA s/A G aA s,²¹ InA s/InP,²² and CdTe/ZnTe²³ quantum wires. Note that, the present modelling is inapplicable to the free-standing quantum wires, where the image charge e ect is extrem ely strong.²⁴

We assume that the lateral con nement is strong, so that only the lowest subband for the electron and hole is occupied. This assumption allows for a reduction of the Schrödinger equation to an elective two-dimensional form. U sually the solution of the trion eigenequations is very challenging and requires extensive variational calculations^{2,3,4,6,7,12,16,17} or application of the quantum M onte C arbom ethods.^{10,15} The present problem is unique in the sense that it allows for an exact inclusion of the interparticle correlations.

The paper is organized as follows: the next Section contains the theory, the results are given in Section III, the conclusion and sum m ary are presented in Section IV.

II. THEORY

We adopt the donor units, i.e., donor Bohr radius $a_d = 4_{-0} h^2 = m_e e^2$ for the unit of length and twice the donor Rydberg $2R_d = h^2 = m_e a_d^2$ as the unit of the energy, where m_e is the band electron e ective m ass and is the dielectric constant. In these units, the H am iltonian for a single electron in a quantum wire with harm onic oscillator lateral con nem ent has the form

$$H_{e} = \frac{1}{2} \frac{\theta^{2}}{\theta z_{e}^{2}} + H_{e}^{1};$$
 (1)

with the lateral H am iltonian

$$H_{e}^{1} = \frac{1}{2} \frac{\theta^{2}}{\theta x_{e}^{2}} + \frac{\theta^{2}}{\theta y_{e}^{2}} + \frac{1}{2t_{e}^{4}} (x_{e}^{2} + y_{e}^{2}); \quad (2)$$

where l_e is the length of the harm onic oscillator con nement for the electron. The ground-state wave function of the Ham iltonian (2) is $_e = \exp\left[(x^2 + y^2) = 2l_e^2 \right] = l_e^{D}$ with the energy eigenvalue $E_e = 1 = l_e^2$. In the adopted single-band approximation the hole ground-state wave function ($_h$) of the lateral con nement has the form of $_e$ but with l_h -the harm onic oscillator length for the hole instead of l_e , and the energy is $E_h = 1 = l_h^2$, where

= $m_h = m_e$ is the hole to electron e ective mass ratio, or, in other words, the hole mass in the donor units. The negative trion H am iltonian can be written as

$$H = H_{e1} + H_{e2} + H_h - \frac{1}{r_{e1h}} - \frac{1}{r_{e2h}} + \frac{1}{r_{12}}; \quad (3)$$

where r_{elh} (r_{e2h}) is the distance between the rst (second) electron and the hole and r_{12} is the electron-electron distance. We assume that the lateral con nement is sufciently large that the trion wave function can be electron-tively separated into a product

$$(\mathbf{r}_{e1};\mathbf{r}_{e2};\mathbf{r}_{h}) = (\mathbf{x}_{e1};\mathbf{y}_{e1}) (\mathbf{x}_{e2};\mathbf{y}_{e2}) (\mathbf{x}_{h};\mathbf{y}_{h}) (\mathbf{z}_{e1};\mathbf{z}_{e2};\mathbf{z}_{h});$$
(4)

where is the negative trion wave function of the motion along the wire. The H am iltonian (3) integrated over the lateral degrees of freedom with the wave function (4) produces the elective trion H am iltonian:

$$H^{ef} = \frac{1}{2} \frac{\theta^{2}}{\theta z_{e1}^{2}} + \frac{\theta^{2}}{\theta z_{e2}^{2}} - \frac{1}{2} \frac{\theta^{2}}{\theta z_{h}^{2}} + V^{ef}(l_{e}; z_{e1} - z_{e2}) - V^{ef}(l_{eh}; z_{e1} - z_{h})$$

$$V^{ef}(l_{eh}; z_{e2} - z_{h});$$
(5)

with $l_{eh} = \frac{p}{(l_e^2 + l_h^2)=2}$ and the elective interaction potential^{9,25}

$$V^{ef}(l;z) = (=2)^{1=2} \operatorname{erfc}(z; = 2l) \exp(z^2 = 2l^2) = l;$$
 (6)

which is nite at the origin (V ^{ef}(l;0) = 1=1) and approaches the 1=z asymptotic at large z. Hamiltonian (5) is written with respect to the sum of the ground-state energies of noninteracting two electrons and one hole. Therefore, the absolute value of the (negative) energy of a bound state is interpreted as the energy needed to separate all the particles away from one another. Introducing the center-offm ass coordinate $Z = (z_{e1} + z_{e2} + z_h) = (2 +)$ one obtains $H^{ef} = \frac{1}{2M} \frac{e^2}{eZ^2} + H^{rel}$, where M = 2 + is the negative trion m ass and H ^{rel} is the relative m otion H amiltonian

$$H^{\text{rel}} = \frac{1}{2} \frac{\theta^{2}}{\theta z_{h1}^{2}} + \frac{\theta^{2}}{\theta z_{h2}^{2}} \frac{1}{\theta z_{h1}^{2}} \frac{\theta^{2}}{\theta z_{h1} \theta z_{h2}}$$

$$+ V^{\text{ef}}(l_{e}; z_{h1} z_{h2}) V^{\text{ef}}(l_{eh}; z_{h1}) V^{\text{ef}}(l_{eh}; z_{h2});$$

$$(7)$$

with the reduced mass of an electron-hole pair = =(1 +), and the coordinates of the relative electron-hole positions $z_{h1} = z_h \quad z_{e1}$ and $z_{h2} = z_h \quad z_{e2}$. In these coordinates the inter-electron distance along the length of the wire is $z_{12} = j z_{h1} \quad z_{h2} j$. The wave function is separable into a product of the center of mass and relative wave function $(z_{e1}; z_{e2}; z_h) = {}_{CM} (Z) (z_{h1}; z_{h2}).$

The corresponding relative Ham iltonian for the positive trion has the following form :

$$\begin{aligned} H_{+}^{rel} &= \frac{1}{2} \frac{\theta^{2}}{\theta z_{h1}^{2}} + \frac{\theta^{2}}{\theta z_{h2}^{2}} \frac{\theta^{2}}{\theta z_{h1} \theta z_{h2}} \\ &+ V^{ef}(I_{h}; z_{h1} z_{h2}) V^{ef}(I_{eh}; z_{h1}) \\ V^{ef}(I_{eh}; z_{h2}); \end{aligned}$$
(8)

with z_{h1} , z_{h2} standing here for the relative position coordinates of the rst and second hole with respect to the electron position. The reference energy for the H am iltonian (8) is the energy of the dissociated com plex, i.e., $2E_{h} + E_{e}$.

In the following we consider also the exciton for which the e ective H am iltonian written with respect to the energy of a dissociated electron and hole pair reads

$$H^{X} = \frac{1}{2} \frac{\theta^{2}}{\theta z_{eh}^{2}} \quad V^{ef}(\underline{l}_{eh}; z_{eh}):$$
(9)

The lowest eigenvalue of this H am iltonian is equal to m inus the exciton binding energy (E_B^X). On the other hand the di erence between E_B^X and the eigenvalues of trion H am iltonians (7,8) is equal to the trion binding energies (E_B^X , $E_B^{X^+}$) with respect to dissociation into an exciton and a free electron (for X) or a hole (for X⁺). Trion binding energies are equal to the red-shift of the trion recombination lines with respect to the exciton line in the PL spectrum.



FIG.1: (a) [color online] C ontour plot of the interaction potential V = V $^{\rm ef}$ (L; z_{h1} z_{h2}) V $^{\rm ef}$ (L; z_{h1}) V $^{\rm ef}$ (L; z_{h2}) as function of the interparticle distances with lateral con nem ent length L = l_e = l_h = 1. D istances and energies are given in donor units. The dashed-dotted line corresponds to V = 0. (b) The interaction potential plotted for L = 1 along the lines z_{h2} = z_{h1} , z_{h2} = z_{h1} 1.5, and z_{h2} = z_{h1} 3 m arked in (a) with (thick) solid, dotted and dashed lines respectively, as function of the interelectron (X) or interhole (X $^+$) distance z_{12} = z_{h1} z_{h2} . Thin solid line shows the $3=jz_{12}j$ asymptotic.

W e solve the relative H am iltonian eigenequations using the imaginary time technique²⁶ on a two-dimensional grid with a nite-di erence approach. We use 201 points in both z_{h1} and z_{h2} directions. The size of the computational box in both directions is chosen "self-consistently" to be 12 times larger than the average distance be-

tween the particles of the same charge de ned as $(z_{h1} \quad z_{h2}) > 1^{=2}$.

In the present calculations we assumed harm onic oscillator lateral con nem ent which allows us to sim plify the problem considerably because of the availability of analytical form ula^{9,25} for the e ective one-dimensional interaction. The con nem ent lengths le and le param etrize the strength of the particle localization. Since the singleparticle energies cancel in the calculation of the trion binding energies, the applicability of the present results is wider. In fact the present results can be used for any form of the lateral con nem ent (which does not even have to be cylindrically sym m etric) as long as it produces the same e ective interaction potential. For instance the electron-electron interaction potential for $l_e = 2.95$ and 6 nm is very well (i.e. with a precision better than 2%) reproduced for a G aA s quantum wire (m $_{e}$ = 0.067) with a circular square well con nem ent of depth 320 m eV and diam eters 9.6 nm and 22.8 nm respectively. For elliptical harm onic oscillator con nem ent with di erent oscillator lengths in x and y directions $(l_x \text{ and } l_y, \text{ respectively})$ we cannot give a closed analytical form ula for the e ective interaction potential. Nevertheless, we have found via a num erical integration that the interaction potential between two electrons in an elliptical wire can be surprisingly well reproduced by form ula (6) for a circular wire with an e ective $l = (l_x + l_y) = 2$. The num erically calculated deviation between the two potentials is not larger than 2% for any interelectron distance. The essential assum ption of the present m odel therefore does not rely on the form of the lateral con nem ent but on its strength, which has to be large enough to prevent the Coulomb interactions from deforming the lateral wave functions. The applied assumption of the frozen lateral degrees of freedom for the electron and the hole is applicable for the exciton binding energy when $l_e < a_d$ and $l_h < a_d$. This condition guarantees that the length of the lateral connem ent of the carriers is sm aller than the bulk exciton radius, and that the sum of the lateral con nem ent energies for the electron and the hole are at least two times larger than the exciton binding energy in bulk. For trions the applied approximation is better justi ed and the conditions are less stringent because the trions have a larger size and have sm aller binding energies than the exciton.

III. RESULTS

W e start the presentation of our results by discussing the properties of trions in quantum wires with equal lateral con nem ent for the electron and the hole (subsection IIIA), and then in subsection IIIB we show the e ect of di erent con nem ents for the stability of X⁺ and X trions. Subsection IIIC describes the e ect of the m agnetic eld oriented parallel to the axis of the wire.



FIG.2: W ave functions for negative (a,d,g,j) and positive (b,c,e,f,h,i,k,l) trions for $l_e = l_h = L = 0.2$ in z_{h1} and z_{h2} coordinates (horizontal and vertical axis, respectively) for di erent values of the mass ratio . P lots (c,f,i,l) show the wave functions of the excited X⁺ state antisym metric with respect to the interchange of the holes. The dashed line in (f,i,l) shows the node of the wave functions. P lot (c) corresponds to an unbound state, for other plots the computational box is larger than the fragment displayed and the states are bound.

 ${\tt A}$. Identical electron and hole lateral con ${\tt nem ent}$

For equal electron and hole lateral con nem ent ($l_e = l_h = L$) the electron-electron, the hole-hole, and the electron-hole interactions have the same form . The total interaction potential, identical for both types of trions, is plotted in Fig. 1 (a) as function of z_{h1} and z_{h2} for L = 1. The regions of positive (negative) potentials are

plotted with red (blue) colors. Zero of the interaction potential is marked with a dash-dotted line. The interaction potential is minimal along the lines $z_{\rm h1}=0$ and $z_{\rm h2}=0$ at which one of the two electrons and the hole are in the same position (for X $\)$ or the position of one of the holes coincides with the electron position (for X $^+$). The potential is maximal along the diagonal $z_{\rm h1}=z_{\rm h2}$ at which the two particles of the same charge are localized in the same point along the wire length. Fig. 1 (b) shows



FIG. 3: Electron-hole (solid lines), electron-electron, hole-hole (dashed lines) pair correlation functions plots for X and X $^+$ (lines marked by black squares) at ~=~6:72 and l_e = l_h = 0.2.



FIG. 4: B inding energies of the negative (dashed lines) and positive trion (solid lines) states for L = 0.2 as function of the m ass ratio . H igher solid curve corresponds to the X⁺ state antisym m etric with respect to the interchange of electrons and holes, i.e. it is the rst excited state. Thin vertical lines show the values of = 1;1:98;6:72 and 15.2. D otted curve, referred to the right axis, show s the exciton ground-state eigenvalue. Energies and lengths are in donor units.

the cross-sections of the interaction potential along the three straight lines in Fig. 1 (a) as function of the interelectron (X) or interhole (X⁺) distance z_{12} . On the antidiagonal the interaction has the form of a triangular potential well [cf. solid line in Fig. 1 (b)]. Moving along the antidiagonal is equivalent to interchange the position of the two particles of the same charge with xed position of the third particle of the opposite charge. A long the paths plotted with dotted and dashed lines in Fig. 1 (a), which are shifted below the antidiagonal, the potential has the form of a double potential well [see Fig. 1 (b)] with a barrier near the diagonal resulting from the



FIG.5: [color online] Binding energies of the trions as functions of the length of the lateral con nement. Lines for

= 1;1:98;6:72 and 15.2 plotted with black, blue, red, and green colors, respectively. For = 1 binding energies of X and X⁺ are equal. The dashed lines are the energies of the excited X⁺ states antisymmetric with respect to the interchange of the holes (X does not possesses a bound excited state for > 1). Lines for X at = 1:98 and 6.72 have been om itted for clarity - they are situated between the = 1 line and = 15.2 line for X (see Fig. 4). Inset: energy eigenvalues for neutral exciton and charged trions for = 15.2. Energies and lengths are given in donor units.

repulsion of the equally charged particles. For large z_{12} the potential approaches $3=z_{12}$ asymptotically which is shown by the this solid line in Fig. 1(b).

Contourplots of the wave function of the negative and positive trions calculated for di erent e ective m ass ratios are plotted in Fig. 2 for L = 0.2. For L = 1, the negative and positive trion relative H am iltonians (7) and (8) di er only by the factor standing in front of the mixed derivative (1 = for X and 1 for X^+). The ground-state wave function for = 1 is the same for both trions [cf. Figs. 2 (a,b)]. The rst excited state of X⁺, which is antisymmetric with respect to the interchange of the holes is unbound. Its wave function calculated for the size of the computational box 100 100 (in donor Bohr radius units) is plotted in Fig. 2 (c). For the unbound state no com putational box is large enough (i.e. the wave function vanishes only at the ends of the computational box). The wave function is nonzero only near both axis. One of the holes stays at the position of the electron and the other strives to be as far as possible from the other two particles.

Results for = 1:98 plotted in Figs. 2(d-f) correspond to CdTe material parameters ($m_h = 0.19m_0$, $m_e = 0.096m_0$) with the donor units $a_d = 5:4$ nm and $2R_d = 27:6$ meV. The probability density maximum for = 1 is split into two extrem a at the antidiagonal of the plots [cf. Figs. 2(a-b)]. For > 1 these two extrem a merge into a single one for X [see Fig. 2(d)] and for X⁺ they become more distinctly separated [see Fig. 2(e)] and the excited state for X⁺ becomes bound [cf. Fig. 2(f)].



FIG.6: [color online] Contour plot of the interaction potential for (a) negative trion $V = V^{ef}(l_e; z_{h1} z_{h2}) V^{ef}(l_{eh}; z_{h1}) V^{ef}(l_{eh}; z_{h2})$ and (b) positive trion $V = V^{ef}(l_h; z_{h1} z_{h2}) V^{ef}(l_{eh}; z_{h1}) V^{ef}(l_{eh}; z_{h2})$ as function of the interparticle distances for the lateral con new ent lengths $l_e = 1$ and $l_h = 0.5$. Distances and energies are given in donor units.



FIG.7: [color online] Shifts of the trion recombination PL lines with respect to the PL exciton line as function of the hole con nem ent length (l_h) for G aAs. D i erent values of the electron con nem ent length are plotted with di erent colors.

Figs. 2(q-i) and 2(i-1) for = 6:7 and = 152correspond to GaAs ($m_h = 0.45m_0$, $m_e = 0.067m_0$, $2R_d = 11.9 \text{ meV}$, $a_d = 9.8 \text{ nm}$) and InAs (m $_h = 0.41 \text{ m}_0$, $m_{e} = 0.027m_{0}, 2R_{d} = 3.2 \text{ meV}$ and $a_{d} = 29.7 \text{ nm}$) material parameters, respectively. Increasing has an opposite e ect on the X \quad and X $^+$ wave functions. For the negative (positive) trion the localm in im um along the diagonal $z_{h1} = z_{h2}$ is less (m ore) pronounced. The wave function evolution with is related to the tunnelling of the particles of the sam e charge via the potential barrier presented in Fig. 1 (b). The electrons in X with light effective m asses tunnel easily through the diagonal barrier due to the interelectron repulsion. On the other hand the diagonal barrier is e ectively much larger for the heavymass holes which prevents its penetratation at large which leads to the appearance of the characteristic maxin a elongated along the diagonal in Figs. 2(e,h,k).

The correlation between the particles in the com plexes is more clearly visible in the pair correlation functions plotted in Fig. 3. The electron-hole correlation function is calculated as $f_{eh}\left(z\right)=dz_{h1}dz_{h2}j~(z_{h1};z_{h2})\mathring{f}~(z_{z_{h1}})$ and the hole-hole (for $_{R}X^{+}$), and electron-electron (for X) as $f_{sam}~(z)=dz_{h1}dz_{h2}j~(z_{h1};z_{h2})\mathring{f}~[z~(z_{h1}-z_{h2})]$. The Coulom b hole in the hole-hole correlation in X^{+} ism uch larger than for electron-hole localization.

The binding energies of the exciton and the trions for L = 0.2 are plotted as functions of in Fig. 4. All the binding energies are increasing functions of . In bulk the rst excited state of the positive trion is antisym metric with respect to the hole interchange, 27 possess the P symmetry and is bound for > 42. The critical value of the m ass ratio is m uch sm aller for quasi 1D con nem ent.⁹ Here, for L = 0.2 the excited X⁺ state is bound for > 1.2 (see Fig. 3). For quasi1D con nem ent the low est excited state has the S sym m etry with respect to the axis of the wire but is of odd spatial parity, i.e., it is antisymm etric with respect to simultaneous change of sign of all the z coordinates (see Fig. 2). The groundstate of X⁺ becom es degenerate with respect to the sym m etry of the wave function, i.e., the hole interchange, for large for which tunnelling through the diagonal potential barrier (cf. Fig. 1) disappears. At large also the probability density of the excited X + level becom es identical to the ground-state probability density (cf. Fig. 2). does not possesses a bound excited state for > 1. Х

The inset to Fig. 5 shows the ground-state energy for

= 152 as function of the lateral con nem ent length. In the L = 0 lim it the average interparticle distances decrease to zero and the energies diverge to m inus in nity. This is a consequence of the C oulom b interaction singularity in one dimension.²⁸ The main part of Fig. 5 shows the shifts of the trion PL lines with respect to the exciton line (calculated as the di erence of the eigenvalues presented in the inset) for di erent values of . It turns out that the binding energies have a power law dependence on L, i.e. L q , for the X and X $^{+}$ ground state presented in this gure q changes from 0.83 (= 1) to 0.91 (X $^{+}$ for = 15.2).

B. E ect of di erent electron and hole lateral con nem ent

Let us now consider the interaction potential for stronger hole con nem ent. Figs. 6(a) and (b) show the interaction potentials for l_e = 1 as in Fig. 1 but for smaller l_h = 0.5. For both the negative [cf. Fig. 6(a)] and the positive trion [cf. Fig. 6(b)] the potentialm inim a at z_{h1} = 0 and z_{h2} = 0 become deeper with respect to the l_e = l_h case presented in Fig. 1. For X the electron-electron interaction (the diagonal potential barrier) is not a ected by the change of l_h [com pare Fig. 1 and Fig. 6(a)]. On the other hand the hole-hole repulsive interaction for X $^+$ is strongly increased.



FIG.8: [color online] D i erence of the positive and negative trion binding energies (in meV) as function of the electron and hole con nem ent lengths for G aAs material parameters. B lue (red) regions correspond to more stable negative (positive) trion. A bove the dashed-dotted line the negative trion is unbound. The green line corresponds to E_B (X) = 4.2 meV and the yellow line to E_B (X ⁺) = 2.9 meV.

The elect of the hole localization on the trion binding energies is plotted in Fig. 7 for GaAs material parameters and xed values of the electron lateral connement. Consistently with the results of section III.A for $l_e = l_h$ the positive trion is more stable than the negative trion. A decrease of l_h below the value of l_e results in the interchange of the X and X $^+$ energy lines.²⁹ This is due to the enhanced hole-hole interaction shown in Fig. 6 (b). The negative trion binding energy is a monotonous function of the hole connement length, the larger l_h the smaller is the electron-hole interaction stabilizing X.



FIG.9: Interparticle distances for the negative (solid lines) and positive trions (dashed lines) and for the exciton (dotted line) for G aAs m aterial parameters and $l_{e} = 2.95$ nm. (e-e), (e-h), and (h-h) stand for the electron-electron, the electron-hole and the hole-hole distance.

The situation is more complex for X $^+$, since with increasing $l_{\rm h}$ also the destabilizing hole-hole interaction decreases. As a consequence the positive trion binding energy possesses a maximum as function of $l_{\rm h}$.

The di erence of the positive and negative trion binding energies is plotted in Fig. 8. Both the trions are equally stable for $l_{\!h}$ = 0:92 $l_{\!e}$ 0:38 nm . For $l_{\!h}$ larger (smaller) than 0:921, 0:38 nm X⁺ is more (less) stable than X . The maximum of the X^+ binding energy presented in Fig. 7 follows a path that is nearly linear for $l_{e} > 2$ nm and is approximately parametrized by $l_n = 1.62 l_e$ 1.98 nm. For the points at the left of the dash-dotted line the electron-hole attractive interaction stabilizing the trion is so weak with respect to the electron-electron repulsive interaction destabilizing the com plex that the negative trion stops to be bound (see also the line for X at $l_e = 2.95$ nm in Fig. 7). The absence of the negative trion binding requires a substantially weaker hole localization than the localization of the electron which is rather in possible to obtain in the presently produced quantum wires and would require the valence band o set between the wire and the matrix to be much sm aller than the conduction band o set. M oreover, the present m odelling based on the assumption that the lateral wave functions are not a ected by the interaction is likely to fail since the hole wave function is very likely to becom e m ore localized due to the attraction by strongly con ned electrons.

The tofthe calculated X and X⁺ binding energies to the experimental data is obtained at the crossing of the green and yellow lines, i.e., for $l_e = 2.95$ nm and $l_h =$ 1.3 nm. The obtained t corresponds to realistic values which give a general idea on the particle localization in the wire (the measurements¹¹ were performed on a Vgroove G aA s/A IG aA s quantum wire with a thickness of the G aA s crescent of 3 nm at the center). O byiously, a m ore realistic m odel is required to extract details of the con nem ent from the experim ental data.

The dependence of the size of the trion, i.e., the interparticle distance as function of the hole con nement length, is shown in Fig. 9 for $l_e = 2.95$ nm. The electronhole distance for the trions and the exciton have been calculated as $\overline{\langle z_{h1}^2 \rangle}$, and $\overline{\langle z_{eh}^2 \rangle}$, respectively. The hole-hole distance for X + and the electron-electron distance for X are determined as $(z_{h1} z_{h2})^2 > .$ The size of the exciton increases as ln increases which is due to the reduced value of the electron-hole interaction. M uch stronger dependence on l_h is observed for X , which becom es unbound for $l_h > 7$ nm [cf. Fig. 7]. The dependence of the X⁺ size on the hole con nem ent is nonmonotonous. The positively charged complex has the smallest size near $l_h = 3 \text{ nm}$ when it is the most strongly bound [cf. Fig. 7]. For $l_n = l_e = 2.95$ nm the order of the interparticle distances in the two com plexes is the same as in two-dimensional quantum wells (compare Fig. 4 of Ref. $[1^3]$). In spite of the fact that the probability of nding both holes in X^+ in the same position is much smaller than for electrons in X (cf. Fig. 3) the longer tail of the electron-electron correlation function results in a larger electron-electron distance than hole-hole distanœ.



FIG.10: [color on line] M agnetic eld dependence of the trion binding energies in G aAs for di erent values of the electron and hole oscillator lengths.

C. Magnetic eld parallel to the wire

In the present approach it is straightforward to include a magnetic eld oriented parallel to the axis of the wire. It simply scales down the electron and hole oscillator lengths according to the form ula $l(B) = (1=1^4 (0) + 1=1^4)^{1-4}$, where $l_c = \frac{1}{2h=eB}$ is the magnetic eld

length ($l_c = 3628 = B \text{ nm } T$). Since l(B) for high m agnetic elds decreases to l_c , the m agnetic eld tends to equalize the electron and hole localization. The binding energy of the trions can be obtained following paths of $(l_h (B); l_e (B))$ on Fig. (8). The modi cation of the binding energies of the trions by the magnetic eld is presented in Fig. 10 for di erent oscillator lengths. In a magnetic eld of 40 T, 1(B = 0) = 4.9 nm is decreased to 1(B = 40T) = 4:4 nm and 1(B = 0) = 6:86 nm to 1(B = 40T) = 5:19 nm. For $l_e = l_h = 6:86 \text{ nm}$ (see the red curves in Fig. 10) the magnetic eld decreases the length of con nem ent exactly as in the case presented in Fig. 5. In the more realistic case of stronger hole con nement, i.e., for $l_e = 6:86 \text{ nm}$ and $l_h = 4:9 \text{ nm}$ (see the black lines in Fig. 10) the magnetic eld increases the binding energy of the positive trion more strongly. This is because the magnetic eld more strongly a ects the larger le value than the smaller hole localization length le which increases the electron-hole interaction m ore strongly than the repulsive hole-hole potential. For X the e ect of the increased electron-hole interaction is nearly cancelled by the increase of the electron-electron potential value. N ear 35 T a crossing of the black lines is observed, which corresponds to passing from the "blue" to the "red" region on the phase diagram of Fig. 8. This crossing is qualitatively opposite to the one obtained for two-dimensional quantum wells,¹³ in which a sm all magnetic eld (around 1 T) increased the X stability over the X⁺ binding energy. In quantum wells the magnetic-eld related increase of the single-particle energy is smaller for electrons and holes bound in the trion complex than for the lowest Landau level in the nal state of the free electron and hole after the trion dissociation. The crossing of the binding energies observed in quantum wires¹³ is therefore at least partially due to the stronger dependence of the electron lowest Landau level { note an alm ost linear magnetic eld dependence of the trion binding energies in Fig. 2 of Ref. $[1^3]$. In the present calculations the free electron and the free hole are strongly localized in the plane perpendicular to the eld and the single-particle magnetic eld e ects cancel due to the assumption of the frozen-lateral degrees of freedom, so that the crossing is entirely due to the modi ed e ective inter-particle interactions.

In the case of stronger electron con nem ent ($l_e = 4.9$ nm, $l_h = 6.86$ nm { the blue lines in Fig. 10) the situation is just opposite, the X is less strongly bound and the magnetic eld acts more strongly on the negative trion decreasing the binding energy di erence according to the mechanism described above. However, for the electron con nem ent equalor stronger than the hole con nem ent, the magnetic eld does not lead to crossing of the trion energy lines and X $^+$ is more stable for any magnetic eld.

W e studied the properties of the negative and positive trions in quantum wires with strong lateral con nem ent using the approxim ation of the lowest subband occupancy which allows for a num erically exact solution of the multi-particle Schrodinger equation. W e investigated the relative stability of the positive and negative trions with respect to the dissociation into an exciton and a free carrier for di erent electron and hole con nem ent. W e found that the order of the negative and positive trion P L lines is interchanged when the lateral con nem ent of the hole is stronger than the one for the electron. In a G aA s quantum wire with $l_{p} = 5$ nm we predict that when l_{p} is 20% sm aller the positive and negative trion recombination lines interchange. The change in the order is due to modi cation of the e ective interactions in the trion com plexes. The present results provide an explanation

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for the recently experim entally observed larger stability of the negative trion in quantum wires.¹¹ W e predict that for larger X stability due to stronger hole con nem ent the magnetic eld oriented parallel to the axis will tend to interchange the order of the X⁺ and X energy lines.

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